L Number	Hits	Search Text	DB	Time stamp
58	4		LICDAT.	2004/09/15
30	4	gunn and pinguet	USPAT;	
			US-PGPUB;	13:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
59	2	gunn and pinguet and germanium	USPAT;	2004/09/15
			US-PGPUB;	13:37
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
60	6	luxtera	USPAT;	2004/09/15
			US-PGPUB;	13:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
61	2	luxtera and germanium	USPAT;	2004/09/15
			US-PGPUB;	13:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
62	0	(waveguide same (core with germanium	USPAT;	2004/09/15
		with silicon with heterojunction))	US-PGPUB;	13:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
63	0	((core with germanium with silicon with	USPAT;	2004/09/15
		heterojunction))	US-PGPUB;	13:41
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
64	0	((core with germanium with	USPAT;	2004/09/15
		heterojunction))	US-PGPUB;	13:41
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
65	2243	((core with germanium))	USPAT;	2004/09/15
		(	US-PGPUB;	13:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
66	219	waveguide same cladding with ((core with	USPAT;	2004/09/15
		germanium))	US-PGPUB;	13:42
		go:a,,	EPO; JPO;	10142
			DERWENT;	
			IBM_TDB	
67	295	waveguide same cladding same ((core with	USPAT;	2004/09/15
~'	293	germanium))	US-PGPUB;	13:42
		_ gea,; 	1	13.74
			EPO; JPO;	
			DERWENT; IBM_TDB	

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68	0	waveguide same cladding same ((core with	USPAT;	2004/09/15
		germanium)) same heterojunction	US-PGPUB;	13:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
69	63	waveguide same cladding same ((core with	USPAT;	2004/09/15
		germanium) with silicon)	US-PGPUB;	13:43
		<b>3</b>	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
70	0	waveguide same (cladding with (insulating	USPAT;	2004/09/15
		or dielectric)) same ((core with germanium)	US-PGPUB;	13:43
		with silicon)	EPO; JPO;	10110
		With Silloun,	DERWENT;	
			IBM_TDB	
71	63	waveguide same (cladding) same ((core	USPAT;	2004/09/15
• •		waveguide same (clauding) same ((core with germanium) with silicon)	US-PGPUB;	13:44
	-	with germaniani, with smooth,	EPO; JPO;	10.77
			DERWENT;	
1			IBM_TDB	
72	0	wayanyida aama (aladdina) aama (laara	_	2004/09/15
12		waveguide same (cladding) same ((core	USPAT;	
		with germanium) with silicon) same	US-PGPUB;	13:44
		(dielectric or insulating)	EPO; JPO;	
			DERWENT;	
		, , , , , , , , , , , , , , , , ,	IBM_TDB	
73	63	waveguide same (cladding) same ((core	USPAT;	2004/09/15
		with germanium) with silicon)	US-PGPUB;	13:45
			EPO; JPO;	
]			DERWENT;	
			IBM_TDB	
74	46	waveguide same (cladding) same ((core	USPAT;	2004/09/15
		near10 germanium near10 silicon))	US-PGPUB;	13:45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
75	4	(waveguide same (cladding) same ((core	USPAT;	2004/09/15
		near10 germanium near10 silicon))).clm.	US-PGPUB;	13:47
			EPO; JPO;	
3			DERWENT;	
			IBM_TDB	
76	13176	heterojunction	USPAT;	2004/09/15
			US-PGPUB;	13:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
77	117	silicon adj heterojunction	USPAT;	2004/09/15
	1		US-PGPUB;	13:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

			<del> </del>	
78	0	silicon adj heterojunction and luxtera	USPAT;	2004/09/15
1			US-PGPUB;	13:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
79	3	silicon adj heterojunction and gunn	USPAT;	2004/09/15
			US-PGPUB;	13:47
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
88	468	waveguide and core and cladding and	USPAT;	2004/09/15
		(heterostructure or heterojunction)	US-PGPUB;	13:49
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
89	0	waveguide and core and cladding and	USPAT;	2004/09/15
		(heterostructure or heterojunction) and	US-PGPUB;	13:49
		gunn	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
90	63	(US-6699765-\$ or US-6690871-\$ or	USPAT;	2004/09/15
		US-6690844-\$ or US-6671443-\$ or	US-PGPUB;	13:49
		US-6654511-\$ or US-6646747-\$ or	EPO; JPO;	
		US-6640021-\$ or US-6625348-\$ or	DERWENT	
		US-6611636-\$ or US-6608945-\$ or		
		US-6554491-\$ or US-6556735-\$ or		
		US-6442977-\$ or US-6449420-\$ or		
		US-6396988-\$ or US-6441906-\$ or		
		US-6316281-\$ or US-6389209-\$ or		
		US-6391214-\$ or US-6337937-\$ or		
		US-6355886-\$ or US-6192712-\$ or		
		US-6222951-\$ or US-6075908-\$ or		
		US-5915051-\$ or US-5917981-\$).did. or		
		(US-5841930-\$ or US-5790726-\$ or		
		US-5793913-\$ or US-5708739-\$ or		
		US-5625729-\$ or US-5682455-\$ or		
		US-5495548-\$ or US-5280189-\$ or		
		US-5132811-\$ or US-5347601-\$ or		
		US-4747663-\$ or US-4997246-\$ or		
		US-3843229-\$ or US-6788847-\$ or		
		US-6768856-\$).did. or (US-20040005131-\$ or		
		US-20030235933-\$ or US-20030231851-\$ or		
		US-20030179981-\$ or US-20030176075-\$ or		
		US-20030161571-\$ or US-20030100824-\$ or		
	[	US-20030003735-\$ or US-20020164137-\$ or		
		US-20020154878-\$ or US-20020106174-\$ or	}	
		US-20020021879-\$ or US-20040156590-\$ or		
		US-20040156589-\$ or US-20040092104-\$ or		
	]	US-20040008968-\$).did. or		
		(EP-793121-\$).did. or (JP-09318830-\$).did.		
	1	or (EP-1343199-\$ or EP-793121-\$ or		
	1	US-20040092104-\$ or WO-200282134-\$).did.	<u> </u>	

91	12	((US-6699765-\$ or US-6690871-\$ or	USPAT;	2004/09/15
		US-6690844-\$ or US-6671443-\$ or	US-PGPUB;	13:50
		US-6654511-\$ or US-6646747-\$ or	EPO; JPO;	
		US-6640021-\$ or US-6625348-\$ or	DERWENT;	
		US-6611636-\$ or US-6608945-\$ or	IBM_TDB	
		US-6554491-\$ or US-6556735-\$ or	, , , , , , , , , , , , , , , , , , , ,	
		US-6442977-\$ or US-6449420-\$ or		
		US-6396988-\$ or US-6441906-\$ or		
		US-6316281-\$ or US-6389209-\$ or		
		US-6391214-\$ or US-6337937-\$ or		
		US-6355886-\$ or US-6192712-\$ or		
		US-6222951-\$ or US-6075908-\$ or		
		US-5915051-\$ or US-5917981-\$).did. or		
		(US-5841930-\$ or US-5790726-\$ or		
		US-5793913-\$ or US-5708739-\$ or		
		US-5625729-\$ or US-5682455-\$ or		
		US-5495548-\$ or US-5280189-\$ or		
		US-5132811-\$ or US-5347601-\$ or		
		US-4747663-\$ or US-4997246-\$ or		
		US-3843229-\$ or US-6788847-\$ or		
		US-6768856-\$).did. or (US-20040005131-\$ or		
		US-20030235933-\$ or US-20030231851-\$ or		
		US-20030179981-\$ or US-20030176075-\$ or		
		US-20030161571-\$ or US-20030100824-\$ or		
		US-20030003735-\$ or US-20020164137-\$ or		
		US-20020154878-\$ or US-20020106174-\$ or		
		US-20020021879-\$ or US-20040156590-\$ or		
		US-20040156589-\$ or US-20040092104-\$ or		
		US-20040008968-\$).did. or		
		(EP-793121-\$).did. or (JP-09318830-\$).did.		
		or (EP-1343199-\$ or EP-793121-\$ or		
		US-20040092104-\$ or		
		WO-200282134-\$).did.) and (heterostructure		
	ŀ	or heterojunction)		
92	o	"10600563" and (heterostructure or	USPAT;	2004/09/15
		heterojunction)	US-PGPUB;	13:50
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
93	0	"10/600563" and (heterostructure or	USPAT;	2004/09/15
		heterojunction)	US-PGPUB;	13:51
		<b>4,</b>	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
94	0	"10/600563"	USPAT;	2004/09/15
			US-PGPUB;	13:50
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
				<u> </u>

95	20576	heterostructure or heterojunction	USPAT;	2004/09/15
		_	US-PGPUB;	13:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
96	637	(heterostructure or heterojunction) near10	USPAT;	2004/09/15
		((si/ge) or (silicon/germanium) or	US-PGPUB;	13:52
		germanium)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
97	1	(heterostructure or heterojunction) near10	USPAT;	2004/09/15
		((si/ge) or (silicon/germanium) or	US-PGPUB;	13:52
		germanium) and luxtera	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
98	4	(heterostructure or heterojunction) near10	USPAT;	2004/09/15
		((si/ge) or (silicon/germanium) or	US-PGPUB;	13:53
		germanium) and (gunn or luxtera)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
99	0	((heterostructure or heterojunction) near10	USPAT;	2004/09/15
		((si/ge) or (silicon/germanium) or	US-PGPUB;	13:56
		germanium)) same waveguide same	EPO; JPO;	
		cladding same core same (insulating or	DERWENT;	
400		dielectric)	IBM_TDB	0004/00/45
100	1	(core with (heterostructure or	USPAT;	2004/09/15
		heterojunction) near10 ((si/ge) or	US-PGPUB;	13:56
		(silicon/germanium) or germanium))	EPO; JPO;	
			DERWENT;	
101	4	(core with (heterostructure or	USPAT;	2004/09/15
.0.	_	heterojunction or hetero-structure or	US-PGPUB;	14:01
		hetero-junction) with ((si/ge) or	EPO; JPO;	14.01
		(silicon/germanium) or germanium))	DERWENT:	
		(one-on-gormaniani) or gormaniani),	IBM_TDB	
102	652	((heterojunction or hetero-junction) with	USPAT;	2004/09/15
		((si/ge) or (silicon/germanium) or	US-PGPUB;	14:01
		germanium))	EPO; JPO;	
		, <del>-</del>	DERWENT;	
			IBM_TDB	
103	O	((heterojunction or hetero-junction) with	USPAT;	2004/09/15
		((si/ge) or (silicon/germanium) or	US-PGPUB;	14:02
		germanium)) same core	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
104	1	((heterojunction or hetero-junction) with	USPAT;	2004/09/15
		((si/ge) or (silicon/germanium) or	US-PGPUB;	14:03
		germanium)) same (waveguide or core or	EPO; JPO;	
		cladding)	DERWENT;	
			IBM_TDB	

105	0	core near10 (silicon adj layer) near10	USPAT;	2004/09/15
		(germanium adj layer)	US-PGPUB;	14:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
106	0	core with (silicon adj layer) near10	USPAT;	2004/09/15
		(germanium adj layer)	US-PGPUB;	14:04
		(3	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
107	0	core with (silicon adj layer) with	USPAT;	2004/09/15
		(germanium adj layer)	US-PGPUB;	14:04
		(germamum auj rayer)	EPO; JPO;	14:04
			DERWENT;	
108	3		IBM_TDB	2004/09/15
106	3	core with (silicon) with (germanium adj	USPAT;	:::
		layer)	US-PGPUB;	14:04
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
109	295	core with (silicon) with (germanium)	USPAT;	2004/09/15
			US-PGPUB;	14:04
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
110	131	(core with (silicon) with (germanium)) same	USPAT;	2004/09/15
		cladding	US-PGPUB;	14:05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
111	63	(core with (silicon) with (germanium)) same	USPAT;	2004/09/15
		cladding same waveguide	US-PGPUB;	14:05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
112	5	((core with (silicon) with (germanium))	USPAT;	2004/09/15
		same cladding same waveguide).clm.	US-PGPUB;	14:06
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
113	11	(silicon adj layer) and (germanium adj layer)	USPAT;	2004/09/15
	}	and cladding and core and waveguide	US-PGPUB;	14:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
114	o	germanium adj on adj silicon adj	USPAT;	2004/09/15
		heterojunction	US-PGPUB;	14:12
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

115	160	germanium near silicon near heterojunction	USPAT;	2004/09/15
			US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
116	0	core with (germanium near silicon near	USPAT;	2004/09/15
		heterojunction)	US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
İ			IBM_TDB	
117	0	core with ((ge or germanium) near (si or	USPAT;	2004/09/15
' ' '		silicon) near heterojunction)	US-PGPUB;	14:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
118	0	core with ((ge or germanium) near5 (si or	USPAT;	2004/09/15
		silicon) near5 heterojunction)	US-PGPUB;	14:13
			EPO; JPO;	1-11.0
			DERWENT;	
			IBM_TDB	
119	0	core same ((ge or germanium) near5 (si or	USPAT;	2004/09/15
		silicon) near5 heterojunction)	US-PGPUB;	14:13
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
120	437	((ge or germanium) near5 (si or silicon)	USPAT;	2004/09/15
		near5 heterojunction)	US-PGPUB;	14:13
	1	·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
121	1 1	((ge or germanium) near5 (si or silicon)	USPAT;	2004/09/15
		near5 heterojunction) and core and	US-PGPUB;	14:14
		cladding and waveguide	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
122	o	(core with ((silicon or si) adj layer)) with	USPAT;	2004/09/15
		((germanium or ge) adj layer)	US-PGPUB;	14:15
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
123	o	core with ((silicon or si) adj layer) with	USPAT;	2004/09/15
		((germanium or ge) adj layer)	US-PGPUB;	14:15
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
124	1	core same ((silicon or si) adj layer) with	USPAT;	2004/09/15
_		((germanium or ge) adj layer)	US-PGPUB;	14:16
		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

		<del></del>	T	,
125	6	core and cladding and ((silicon or si) adj	USPAT;	2004/09/15
		layer) with ((germanium or ge) adj layer)	US-PGPUB;	14:18
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
126	6	luxtera	USPAT;	2004/09/15
			US-PGPUB;	14:19
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
127	3	luxtera and (germanium or ge)	USPAT;	2004/09/15
			US-PGPUB;	14:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
128	1014	(germanium adj layer) not near2 silicon	USPAT;	2004/09/15
			US-PGPUB;	14:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
129	3255	((germanium or ge) adj layer)	USPAT;	2004/09/15
			US-PGPUB;	14:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
130	1572	((germanium or ge) adj layer) near (silicon	USPAT;	2004/09/15
		or si)	US-PGPUB;	14:21
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
131	1683	(((germanium or ge) adj layer) ) not	USPAT;	2004/09/15
		(((germanium or ge) adj layer) near (silicon	US-PGPUB;	14:22
		or si) )	EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
132	148	((((germanium or ge) adj layer) ) not	USPAT;	2004/09/15
		(((germanium or ge) adj layer) near (silicon	US-PGPUB;	14:22 `
		or si) )) and (photodetector or waveguide)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
133	41	((((germanium or ge) adj layer) ) not	USPAT;	2004/09/15
		(((germanium or ge) adj layer) near (silicon	US-PGPUB;	14:22
		or si) )) and (photodetector or waveguide)	EPO; JPO;	
		and cladding	DERWENT;	
			IBM_TDB	
134	23	((((germanium or ge) adj layer) ) not	USPAT;	2004/09/15
		(((germanium or ge) adj layer) near (silicon	US-PGPUB;	14:41
		or si) )) and (photodetector or waveguide)	EPO; JPO;	
		and cladding and core	DERWENT;	
L			IBM_TDB	

135	1424	((silicon or si) adj layer) and ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:43
136	1311	(((silicon or si) adj layer) and ((germanium or ge) adj layer) ) and ((silicon or si) near2 (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47
137	113	(((silicon or si) adj layer) and ((germanium or ge) adj layer) ) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) and ((silicon or si) near2 (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47
		)		,

138	5	((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) and ((silicon or si) near2 (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:45
		)		
		) and (photodetector or waveguide)		
139	5	((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer) )	USPAT; US-PGPUB; EPO; JPO;	2004/09/15 14:47
		and ((silicon or si) near2 (germanium or ge))	DERWENT; IBM_TDB	
		)		
		) and (photodetector or waveguide)		

140	3	((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) and ((silicon or si) near2 (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47
141	1240	) and (photodetector or waveguide) and cladding (((silicon or si) adj layer) and ((germanium or ge) adj layer) ) and ((silicon or si) near (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47
142	184	(((silicon or si) adj layer) and ((germanium or ge) adj layer) ) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) and ((silicon or si) near (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:48
		)		

143	4	((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer) ) and ((silicon or si) near (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:48
144	1424	) and cladding ((silicon or si) adj layer) and ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 14:49
145	33	((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 14:49
146	18	((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/15 14:49
147	15	((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core and (waveguide or photodetector)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:26
148	6	(((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core and (waveguide or photodetector)) and (silicon near5 (contact or conducting or conductive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:27
149	6	(((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core and (waveguide or photodetector)) and (silicon near10 (contact or conducting or conductive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:28

150	85	(US-6699765-\$ or US-6690871-\$ or	USPAT;	2004/09/15
	1	US-6690844-\$ or US-6671443-\$ or	US-PGPUB;	15:28
	ļ	US-6654511-\$ or US-6646747-\$ or	EPO; JPO;	
		US-6640021-\$ or US-6625348-\$ or	DERWENT	
		US-6611636-\$ or US-6608945-\$ or		
		US-6554491-\$ or US-6556735-\$ or		
		US-6442977-\$ or US-6449420-\$ or		
		US-6396988-\$ or US-6441906-\$ or		
		US-6316281-\$ or US-6389209-\$ or		
		US-6391214-\$ or US-6337937-\$ or		
		US-6355886-\$ or US-6192712-\$ or		
		US-6222951-\$ or US-6075908-\$ or		
		US-5915051-\$ or US-5917981-\$).did. or		
		(US-5841930-\$ or US-5790726-\$ or		
		US-5793913-\$ or US-5708739-\$ or		
		US-5625729-\$ or US-5682455-\$ or		
		US-5495548-\$ or US-5280189-\$ or		
		US-5132811-\$ or US-5347601-\$ or		
		US-4747663-\$ or US-4997246-\$ or		
		US-3843229-\$ or US-6788847-\$ or		
		US-6768856-\$ or US-6158901-\$ or		
		US-6734453-\$ or US-6684007-\$ or		
		US-5533156-\$ or US-5465312-\$ or		
		US-6075253-\$ or US-6472594-\$ or		
		US-5861324-\$ or US-5681402-\$ or		
		US-6463088-\$ or US-4717225-\$ or		
		US-4715875-\$).did. or (US-4711525-\$ or		
		US-4597787-\$ or US-4426129-\$ or		
		US-4261771-\$ or US-4205329-\$).did. or		
		(US-20040005131-\$ or US-20030235933-\$ or		
		US-20030231851-\$ or US-20030179981-\$ or		
		US-20030176075-\$ or US-20030161571-\$ or		
		US-20030100824-\$ or US-20030003735-\$ or		
		US-20020164137-\$ or US-20020154878-\$ or		
		US-20020106174-\$ or US-20020021879-\$ or		
		US-20040156590-\$ or US-20040156589-\$ or		
		US-20040092104-\$ or US-20040008968-\$ or		
		US-20040056243-\$ or US-20020048289-\$ or		
		US-20020028045-\$).did. or		
		(EP-793121-\$).did. or (JP-09318830-\$ or		
		JP-59141276-\$).did. or (EP-1343199-\$ or		
		EP-793121-\$ or US-20040092104-\$ or		
		WO-200282134-\$ or US-20030102469-\$).did.		

151	24	((US-6699765-\$ or US-6690871-\$ or	USPAT;	2004/09/15
		US-6690844-\$ or US-6671443-\$ or	US-PGPUB;	15:29
		US-6654511-\$ or US-6646747-\$ or	EPO; JPO;	
		US-6640021-\$ or US-6625348-\$ or	DERWENT;	
		US-6611636-\$ or US-6608945-\$ or	IBM_TDB	
		US-6554491-\$ or US-6556735-\$ or		
		US-6442977-\$ or US-6449420-\$ or		
		US-6396988-\$ or US-6441906-\$ or		
		US-6316281-\$ or US-6389209-\$ or		
		US-6391214-\$ or US-6337937-\$ or		
		US-6355886-\$ or US-6192712-\$ or		
		US-6222951-\$ or US-6075908-\$ or		
		US-5915051-\$ or US-5917981-\$).did. or		
		(US-5841930-\$ or US-5790726-\$ or		
		US-5793913-\$ or US-5708739-\$ or		
		US-5625729-\$ or US-5682455-\$ or		
		US-5495548-\$ or US-5280189-\$ or		
		US-5132811-\$ or US-5347601-\$ or		
		US-4747663-\$ or US-4997246-\$ or		
		US-3843229-\$ or US-6788847-\$ or		
		US-6768856-\$ or US-6158901-\$ or		
		US-6734453-\$ or US-6684007-\$ or		
		US-5533156-\$ or US-5465312-\$ or		
		US-6075253-\$ or US-6472594-\$ or		
		US-5861324-\$ or US-5681402-\$ or		
		US-6463088-\$ or US-4717225-\$ or		
		US-4715875-\$).did. or (US-4711525-\$ or		
		US-4597787-\$ or US-4426129-\$ or		
		US-4261771-\$ or US-4205329-\$).did. or		
		(US-20040005131-\$ or US-20030235933-\$ or		
		US-20030231851-\$ or US-20030179981-\$ or		
		US-20030176075-\$ or US-20030161571-\$ or		
		US-20030100824-\$ or US-20030003735-\$ or		
		US-20020164137-\$ or US-20020154878-\$ or		
		US-20020106174-\$ or US-20020021879-\$ or		
		US-20040156590-\$ or US-20040156589-\$ or		
		US-20040092104-\$ or US-20040008968-\$ or		
		US-20040056243-\$ or US-20020048289-\$ or		
		US-20020028045-\$).did. or		
		(EP-793121-\$).did. or (JP-09318830-\$ or		
		JP-59141276-\$).did. or (EP-1343199-\$ or		
		EP-793121-\$ or US-20040092104-\$ or		
		WO-200282134-\$ or		
		US-20030102469-\$).did.) and (silicon near10		
		(contact or conducting or conductive))		

152	2	((US-6699765-\$ or US-6690871-\$ or	USPAT;	2004/09/15
		US-6690844-\$ or US-6671443-\$ or	US-PGPUB;	15:29
		US-6654511-\$ or US-6646747-\$ or	EPO; JPO;	
		US-6640021-\$ or US-6625348-\$ or	DERWENT;	
		US-6611636-\$ or US-6608945-\$ or	IBM_TDB	
		US-6554491-\$ or US-6556735-\$ or		
		US-6442977-\$ or US-6449420-\$ or		
		US-6396988-\$ or US-6441906-\$ or		
		US-6316281-\$ or US-6389209-\$ or		
	i	US-6391214-\$ or US-6337937-\$ or		
		US-6355886-\$ or US-6192712-\$ or		
		US-6222951-\$ or US-6075908-\$ or		
		US-5915051-\$ or US-5917981-\$).did. or		
		(US-5841930-\$ or US-5790726-\$ or		
		US-5793913-\$ or US-5708739-\$ or		
		US-5625729-\$ or US-5682455-\$ or		
		US-5495548-\$ or US-5280189-\$ or		
		US-5132811-\$ or US-5347601-\$ or		
		US-4747663-\$ or US-4997246-\$ or		
		US-3843229-\$ or US-6788847-\$ or		
	1	US-6768856-\$ or US-6158901-\$ or		
		US-6734453-\$ or US-6684007-\$ or		
	]	US-5533156-\$ or US-5465312-\$ or		
		US-6075253-\$ or US-6472594-\$ or		
		US-5861324-\$ or US-5681402-\$ or		
		US-6463088-\$ or US-4717225-\$ or		
ļ		US-4715875-\$).did. or (US-4711525-\$ or		
		US-4597787-\$ or US-4426129-\$ or		
	i	US-4261771-\$ or US-4205329-\$).did. or		
	İ	(US-20040005131-\$ or US-20030235933-\$ or		
		US-20030231851-\$ or US-20030179981-\$ or		
		US-20030176075-\$ or US-20030161571-\$ or		
		US-20030100824-\$ or US-20030003735-\$ or		
		US-20020164137-\$ or US-20020154878-\$ or		
		US-20020106174-\$ or US-20020021879-\$ or		
		US-20040156590-\$ or US-20040156589-\$ or		
		US-20040092104-\$ or US-20040008968-\$ or		
		US-20040056243-\$ or US-20020048289-\$ or		
		US-20020028045-\$).did. or		
		(EP-793121-\$).did. or (JP-09318830-\$ or		
		JP-59141276-\$).did. or (EP-1343199-\$ or		
		EP-793121-\$ or US-20040092104-\$ or		
		WO-200282134-\$ or		
		US-20030102469-\$).did.) and (((si or silicon)		
		adj layer) near10 (contact or conducting or		
L		conductive))		